ABSTRACT

The present invention provides a method of making CSP type semiconductor devices by the use of an general-purpose gang bonding type bonder while improving the yield. The method includes the steps of forming an imitation film carrier tape (20), disposing the imitation film carrier tape (20) relative to a semiconductor chip (12) so that an imitation junction (26a) and an electrode (13) face in a direction of opposing each other, positioning the imitation junctions (26a) with the electrode (13) while being observed through an aperture (22), removing the imitation film carrier tape (20) from the semiconductor chip and disposing a film carrier tape (30) at the same position as occupied by the imitation film carrier tape (20).